



FDV303N Information



For Reference Only

Part Number FDV303N

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 25V 680MA SOT-23

Package TO-236-3, SC-59, SOT-23-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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FDV303N Specifications

Manufacturer Part Number FDV303N Manufacturer Fairchild/ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-236-3, SC-59, SOT-23-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 25V Current - Continuous Drain (Id) @ 25°C 680mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 2.7V, 4.5V Vgs(th) (Max) @ Id 1.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 2.3nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 50pF @ 10V Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 350mW (Ta) Rds On (Max) @ Id, Vgs 450 mOhm @ 500mA, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23 Package / Case TO-236-3, SC-59, SOT-23-3 Report errors?		
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FET Type Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Brive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vds Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Surplier Device Package Package / Case N-Channel MOSFET (Metal Oxide) MOSFET (Metal Oxide) AMOSFET (Metal Oxide) MOSFET (Metal Oxide) AMOSFET (Metal Oxide) AMOSFET (Metal Oxide) AMOSFET (Metal Oxide) ASSUM ASSUM ASSUM SUPS (Assum) Supplier Device Package SOT-23 Package / Case	Package	TO-236-3, SC-59, SOT-23-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)25VCurrent - Continuous Drain (Id) @ 25°C680mA (Ta)Drive Voltage (Max Rds On, Min Rds On)2.7V, 4.5VVgs(th) (Max) @ Id1.5V @ 250μAGate Charge (Qg) (Max) @ Vgs2.3nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds50pF @ 10VVgs (Max)±8VFET Feature-Power Dissipation (Max)350mW (Ta)Rds On (Max) @ Id, Vgs450 mOhm @ 500mA, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23Package / CaseTO-236-3, SC-59, SOT-23-3	Series	-
Drain to Source Voltage (Vdss)25VCurrent - Continuous Drain (Id) @ 25°C680mA (Ta)Drive Voltage (Max Rds On, Min Rds On)2.7V, 4.5VVgs(th) (Max) @ Id1.5V @ 250μAGate Charge (Qg) (Max) @ Vgs2.3nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds50pF @ 10VVgs (Max)±8VFET Feature-Power Dissipation (Max)350mW (Ta)Rds On (Max) @ Id, Vgs450 mOhm @ 500mA, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23Package / CaseTO-236-3, SC-59, SOT-23-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 2.7V, 4.5V Vgs(th) (Max) @ Id 1.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 1.5V @ 250μA Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±8V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 450 mOhm @ 500mA, 4.5V Operating Temperature Supplier Device Package Package / Case 680mA (Ta) 6	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)2.7V, 4.5VVgs(th) (Max) @ Id1.5V @ 250μAGate Charge (Qg) (Max) @ Vgs2.3nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds50pF @ 10VVgs (Max)±8VFET Feature-Power Dissipation (Max)350mW (Ta)Rds On (Max) @ Id, Vgs450 mOhm @ 500mA, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23Package / CaseTO-236-3, SC-59, SOT-23-3	Drain to Source Voltage (Vdss)	25V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 1.5V @ 250μA 2.3nC @ 4.5V 50pF @ 10V +8V FET West of the second se	Current - Continuous Drain (Id) @ 25°C	680mA (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 50pF @ 10V Vgs (Max) ±8V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-236-3, SC-59, SOT-23-3	Drive Voltage (Max Rds On, Min Rds On)	2.7V, 4.5V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Surface Mount Supplier Device Package Package / Case 50pF @ 10V 50pF @ 10PF @ 10V 50pF @ 10PF @ 10	Vgs(th) (Max) @ Id	1.5V @ 250μA
Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 350mW (Ta) Rds On (Max) @ Id, Vgs 450 mOhm @ 500mA, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23 Package / Case TO-236-3, SC-59, SOT-23-3	Gate Charge (Qg) (Max) @ Vgs	2.3nC @ 4.5V
FET Feature - Power Dissipation (Max) 350mW (Ta) Rds On (Max) @ Id, Vgs 450 mOhm @ 500mA, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23 Package / Case TO-236-3, SC-59, SOT-23-3	Input Capacitance (Ciss) (Max) @ Vds	50pF @ 10V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-236-3, SC-59, SOT-23-3	Vgs (Max)	±8V
Rds On (Max) @ Id, Vgs450 mOhm @ 500mA, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23Package / CaseTO-236-3, SC-59, SOT-23-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23 Package / Case TO-236-3, SC-59, SOT-23-3	Power Dissipation (Max)	350mW (Ta)
Mounting Type Surface Mount Supplier Device Package SOT-23 Package / Case TO-236-3, SC-59, SOT-23-3	Rds On (Max) @ Id, Vgs	450 mOhm @ 500mA, 4.5V
Supplier Device Package SOT-23 Package / Case TO-236-3, SC-59, SOT-23-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-236-3, SC-59, SOT-23-3	Mounting Type	Surface Mount
	Supplier Device Package	SOT-23
Report errors?	Package / Case	TO-236-3, SC-59, SOT-23-3
		Report errors?

FDV303N Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FDV303N Payment Methods





















FDV303N Shipping Methods













If you have any question about FDV303N, please do not hesitate to contact us!

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